

13.56 MHz Hollow Cathode Plasma Source HCD-L 300

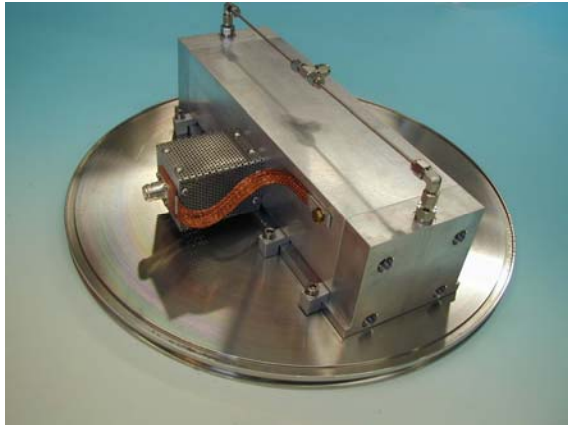


Fig. 1: HCD-L 300

CVD system, resulted in deposition rates as high as 27nm/sec. (author abst.)

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SiO_x Thin Film Deposition Using a Hollow Cathode Plasma Source

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The work described below was performed using a PlasmaConsult HCD-L 300 hollow cathode plasma source.

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*SiO_x Thin Film Deposition Using a Hollow
Cathode Plasma Source*

Abstract

This paper describes the features of a HCD (Hollow Cathode Discharge) plasma source and the characteristics of SiO_x thin films deposited by a plasma source. HCD plasma sources are suitable for high-speed Chemical Vapor Deposition (CVD), such as industrially SiO_x deposition processes. Such processes can be operated at low temperatures, and are suitable to substrate that can not deal well with high temperatures (such as plastics or resins). Application of the HCD plasma